INTEGRATED CIRCUITS

DATA SHEET

74LV11Triple 3-input AND gate

Product data Supersedes data of 1998 Apr 20





Triple 3-input AND gate

74LV11

FEATURES

- Optimized for Low Voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between V_{CC} = 2.7 V and V_{CC} = 3.6 V
- \bullet Typical V_{OLP} (output ground bounce) < 0.8 V at V_{CC} = 3.3 V, $T_{amb} = 25 \, ^{\circ}C$
- Typical V_{OHV} (output V_{OH} undershoot) > 2 V at V_{CC} = 3.3 V, $T_{amb} = 25 \, ^{\circ}C$
- Output capability: standard
- I_{CC} category: SSI

DESCRIPTION

The 74LV11 is a low-voltage Si-gate CMOS device and is pin and function compatible with 74HC/HCT11.

The 74LV11 provides the 3-input AND function.

QUICK REFERENCE DATA

GND = 0 V; T_{amb} = 25 °C; t_r = $t_f \le 2.5$ ns

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t _{PHL} /t _{PLH}	Propagation delay nA, nB, nC to nY	$C_L = 15 \text{ pF};$ $V_{CC} = 3.3 \text{ V}$	10	ns
C _I	Input capacitance		3.5	pF
C _{PD}	Power dissipation capacitance per gate	See Notes 1 and 2	18	pF

NOTES:

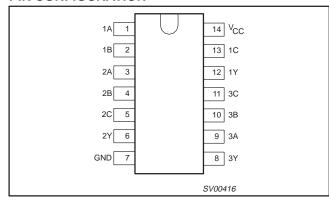
1. C_{PD} is used to determine the dynamic power dissipation (P_D in μ W) $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where: N = number of outputs switching;

 f_i = input frequency in MHz; C_L = output load capacitance in pF; f_o = output frequency in MHz; V_{CC} = supply voltage in V; $\Sigma (C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs. 2. The condition is V_I = GND to V_{CC} .

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	ORDER CODE	PKG. DWG. #
14-Pin Plastic SO	-40 °C to +125 °C	74LV11D	SOT108-1

PIN CONFIGURATION



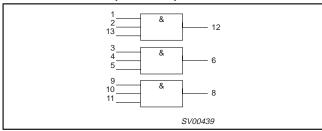
PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
1, 3, 9	1A – 3A	Data inputs
2, 4, 10	1B – 3B	Data inputs
7	GND	Ground (0 V)
12, 6, 8	1Y – 3Y	Data outputs
13, 5, 11	1C – 3C	Data inputs
14	V _{CC}	Positive supply voltage

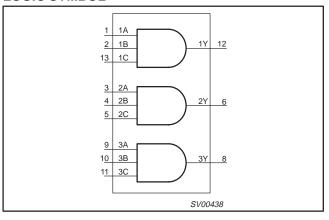
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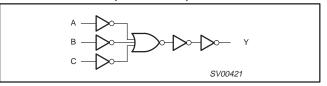
LOGIC SYMBOL (IEEE/IEC)



LOGIC SYMBOL



LOGIC DIAGRAM (ONE GATE)



FUNCTION TABLE

	INPUTS		OUTPUT
nA	nB	nC	nY
L	L	L	L
L	L	Н	L
L	Н	L	L
L	Н	Н	L
н	L	L	L
н	L	Н	L
н	Н	L	L
н	Н	Н	Н

NOTES:

H = HIGH voltage level L = LOW voltage level

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{CC}	DC supply voltage	See Note 1	1.0	3.3	3.6	V
VI	Input voltage		0	-	V _{CC}	V
Vo	Output voltage		0	-	V _{CC}	V
T _{amb}	Operating ambient temperature range in free air	See DC and AC characteristics	-40 -40		+85 +125	°C
		$V_{CC} = 1.0V \text{ to } 2.0V$	-	_	500	ns/V
t _r , t _f	Input rise and fall times	$V_{CC} = 2.0V \text{ to } 2.7V$	-	_	200	ns/V
		$V_{CC} = 2.7V \text{ to } 3.6V$	-	_	100	ns/V

NOTE

The LV is guaranteed to function down to V_{CC} = 1.0 V (input levels GND or V_{CC}); DC characteristics are guaranteed from V_{CC} = 1.2 V to V_{CC} = 3.6 V.

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ABSOLUTE MAXIMUM RATINGS^{1, 2}

In accordance with the Absolute Maximum Rating System (IEC 134). Voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +4.6	V
±I _{IK}	DC input diode current	$V_{I} < -0.5 \text{ or } V_{I} > V_{CC} + 0.5 \text{ V}$	20	mA
±I _{OK}	DC output diode current	$V_{O} < -0.5 \text{ or } V_{O} > V_{CC} + 0.5 \text{ V}$	50	mA
±ΙΟ	DC output source or sink current (standard outputs)	$-0.5V < V_O < V_{CC} + 0.5 V$	25	mA
±I _{GND} , ±I _{CC}	DC V _{CC} or GND current for types with standard outputs		50	mA
T _{stg}	Storage temperature range		-65 to +150	°C
P _{TOT}	Power dissipation per package – plastic mini-pack (SO)	for temperature range: -40 °C to +125 °C above +70 °C derate linearly with 8 mW/K	500	mW

NOTES:

DC CHARACTERISTICS

Over recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

			LIMITS							
SYMBOL	PARAMETER	TEST CONDITIONS	-40) °C to +8	5 °C	–40 °C to	+125 °C	UNIT		
			MIN	TYP ¹	MAX	MIN	MAX			
		V _{CC} = 1.2 V	0.9			0.9				
V _{IH}	HIGH level Input voltage	V _{CC} = 2.0 V	1.4			1.4		V		
	Tonago	V _{CC} = 2.7 V to 3.6 V	2.0			2.0		1		
		V _{CC} = 1.2 V			0.3		0.3			
V _{IL}	LOW level Input voltage	V _{CC} = 2.0 V			0.6		0.6	V		
	romago	V _{CC} = 2.7 V to 3.6 V			0.8		0.8	1		
		$V_{CC} = 1.2 \text{ V}; V_I = V_{IH} \text{ or } V_{IL;} -I_O = 100 \mu\text{A}$		1.2						
	HIGH level output	$V_{CC} = 2.0 \text{ V}; V_I = V_{IH} \text{ or } V_{IL;} -I_O = 100 \mu\text{A}$	1.8	2.0		1.8] _v		
V _{OH}	voltage; all outputs	$V_{CC} = 2.7 \text{ V; } V_I = V_{IH} \text{ or } V_{IL;} -I_O = 100 \mu\text{A}$	2.5	2.7		2.5				
		$V_{CC} = 3.0 \text{ V}; V_I = V_{IH} \text{ or } V_{IL;} -I_O = 100 \mu\text{A}$	2.8	3.0		2.8				
V _{OH}	HIGH level output voltage; STANDARD outputs	$V_{CC} = 3.0 \text{ V}; V_I = V_{IH} \text{ or } V_{IL}; -I_O = 6 \text{ mA}$	2.40	2.82		2.20		V		
		$V_{CC} = 1.2 \text{ V}; V_I = V_{IH} \text{ or } V_{IL}; I_O = 100 \mu\text{A}$		0						
V	LOW level output	$V_{CC} = 2.0 \text{ V}; V_I = V_{IH} \text{ or } V_{IL}; I_O = 100 \mu\text{A}$		0	0.2		0.2	V		
V _{OL}	voltage; all outputs	V_{CC} = 2.7 V; V_I = V_{IH} or V_{IL} ; I_O = 100 μA		0	0.2		0.2	ľ		
		V_{CC} = 3.0 V; V_I = V_{IH} or V_{IL} ; I_O = 100 μA		0	0.2		0.2			
V _{OL}	LOW level output voltage; STANDARD outputs	$V_{CC} = 3.0 \text{ V}; V_I = V_{IH} \text{ or } V_{IL}; I_O = 6 \text{ mA}$		0.25	0.40		0.50	V		
I _I	Input leakage current	$V_{CC} = 3.6 \text{ V}; V_I = V_{CC} \text{ or GND}$			1.0		1.0	μА		
Icc	Quiescent supply current; SSI	$V_{CC} = 3.6 \text{ V}; V_{I} = V_{CC} \text{ or GND}; I_{O} = 0$			20.0		40	μΑ		
Δl _{CC}	Additional quiescent supply current per input	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}; V_{I} = V_{CC} - 0.6 \text{ V}$			500		850	μА		

NOTE:

Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the
device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to
absolute-maximum-rated conditions for extended periods may affect device reliability.

^{2.} The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^{1.} All typical values are measured at T_{amb} = 25 °C.

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AC CHARACTERISTICS

GND = 0V; $t_r = t_f \le 2.5 ns$; $C_L = 50 pF$; $R_L = 1 K\Omega$

			CONDITION			LIMITS					
SYMBOL	PARAMETER	WAVEFORM	CONDITION	-40	-40 °C to +85		–40 °C to +85 °C		-40 °C to +125 °C		UNIT
			V _{CC} (V)	MIN	TYP ¹	MAX	MIN	MAX			
		1.2		60							
	Propagation delay nA, nB, nC to nY	Figures 4 2	2.0		20	39		46			
t _{PHL/PLH} nA, nB, nC to nY	Figures 1, 2	2.7		15	29		34	ns			
			3.0 to 3.6		11 ²	23		27			

NOTES:

- 1. Unless otherwise stated, all typical values are measured at $T_{amb} = 25$ °C.
- 2. Typical values are measured at $V_{CC} = 3.3 \text{ V}$.

AC WAVEFORMS

 $\begin{array}{l} V_M = 1.5 \text{ V at V}_{CC} \geq 2.7 \text{ V} \\ V_M = 0.5 \times V_{CC} \text{ at V}_{CC} < 2.7 \text{ V} \end{array}$

 $V_{\mbox{\scriptsize OL}}$ and $V_{\mbox{\scriptsize OH}}$ are the typical output voltage drop that occur with the output load.

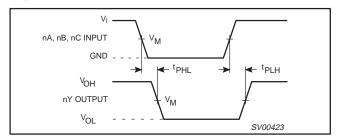


Figure 1. Input (nA, nB, nC) to output (nY) propagation delays.

TEST CIRCUIT

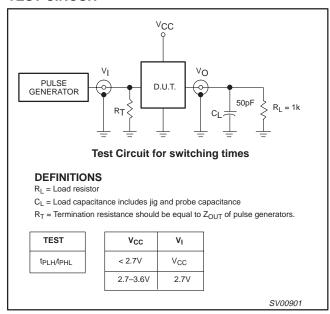


Figure 2. Load circuitry for switching times.

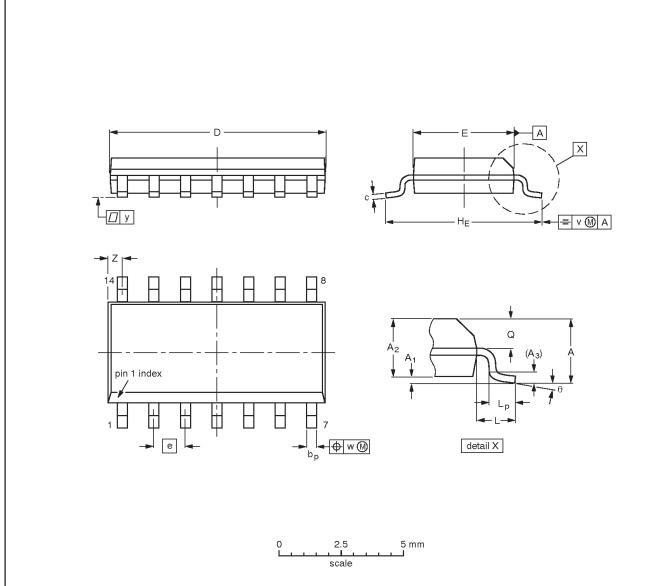
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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	e	HE	L	Lp	Q	>	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.35 0.34	0.16 0.15	0.050	0.244 0.228	0.041	0.039 0.016		0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFEF	EUROPEAN	ISSUE DATE				
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE		
SOT108-1	076E06	MS-012				97-05-22 99-12-27		

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REVISION HISTORY

Rev	Date	Description				
_3	20030304	Product data (9397 750 11194). ECN 853-1894 29487 of 07 February 2003. Supersedes data of 1998 Apr 20 (9397 750 04408).				
		Modifications:				
		Delete DIL, SSOP and TSSOP package ordering and package outlines (discontinued options).				
		Correct power dissipation formula.				
_2	19980420	Product specification (9397 750 04408). ECN 853-1894 19256 of 20 April 1998. Supersedes data of 1997 Feb 03.				

Data sheet status

Level	Data sheet status ^[1]	Product status ^[2] [3]	Definitions
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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^[1] Please consult the most recently issued data sheet before initiating or completing a design.

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^[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.